TECHNICAL DATA DATA SHEET 898, REV. A

HERMETIC POWER SCHOTTKY RECTIFIER Very Low Forward Voltage

Applications:

• Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

Features:

- Soft Reverse Recovery at Low and High Temperature
- Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

Maximum Ratings:

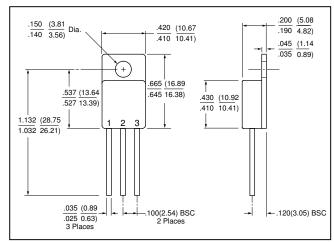
Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	45	V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form (Single/Doubler)	15	Α
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form (Common Cathode/Common Anode)	16	Α
Max. Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine wave (per leg)	75	Α
Max. Thermal Resistance	$R_{\scriptscriptstyle{ hetaJC}}$	(Single)	1.45	°C/W
Max. Thermal Resistance	$R_{ hetaJC}$	(Common Cathode/Common Anode/Doubler) (per leg)	0.72	°C/W
Max. Junction Temperature	Τ _J	-	-65 to +150	°C
Max. Storage Temperature	T _{stg}	-	-65 to +150	°C

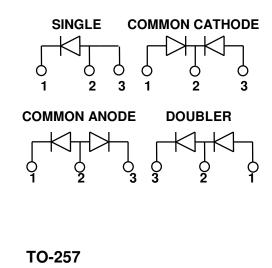
Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 15A, Pulse, T _J = 25 °C (per leg)	0.65	V
	V _{F2}	@ 15A, Pulse, T _J = 125 °C (per leg)	0.60	V
Max. Reverse Current	I _{R1}	$@V_R = 45V$, Pulse, $T_J = 25 ^{\circ}C$ (per leg)	1.5	μΑ
	I _{R2}	$@V_R = 45V, Pulse, T_J = 125 °C (per leg)$	70	mA
Max. Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1 MHz,$ $V_{SIG} = 50 mV (p-p) (per leg)$	800	pF

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Mechanical Dimensions: In Inches / mm

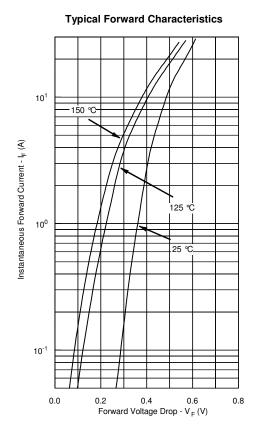


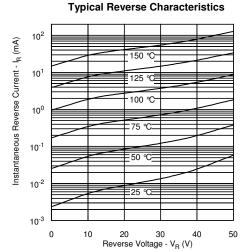


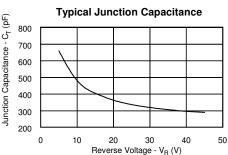
PINOUT TABLE

TYPE	PIN 1	PIN 2	PIN 3
SINGLE RECTIFIER	CATHODE	ANODE	ANODE
DUAL RECTIFIER, COMMON CATHODE (P)	ANODE 1	COMMON CATHODE	ANODE 2
DUAL RECTIFIER, COMMON ANODE (N)	CATHODE 1	COMMON ANODE	CATHODE 2
DUAL RECTIFIER, DOUBLER (D)	ANODE	ANODE/CATHODE	CATHODE

Note: The V_f curves shown are for the SD125SA45 un-packaged die only.









TECHNICAL DATA

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